ALPHA & OMEGA SEMICONDUCTOR

AOT2904/AOB2904

100V N-Channel AlphaSGT™

General Description

- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized fast-switching applications

Applications

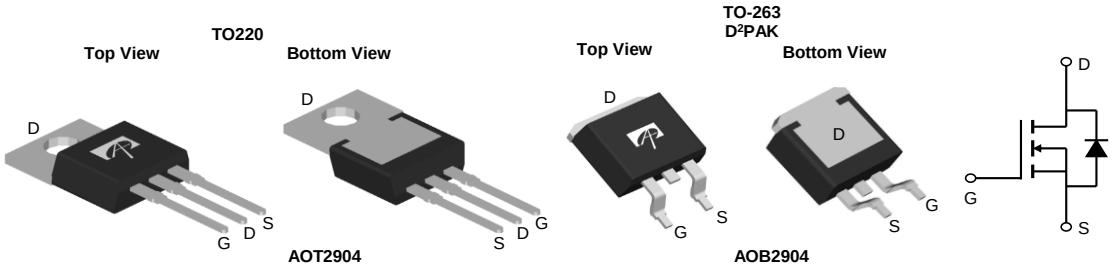
- Industrial
- BMS battery protection
- Synchronous Rectifiers in DC/DC and AC/DC Converters

Product Summary

V_{DS}	100V	
I_D (at V_{GS}=10V)	120A	
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.4mΩ	< 4.2mΩ*
$R_{DS(ON)}$ (at V_{GS}=6V)	< 5.5mΩ	< 5.2mΩ*

100% UIS Tested
100% Rg Tested

RoHS Compliant



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT2904	TO-220	Tube	1000
AOB2904	TO-263	Tape & Reel	800

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current G	T_C=25°C	I_D	120	A
	T_C=100°C		120	
Pulsed Drain Current C		I_{DM}	425	
Continuous Drain Current	T_A=25°C	I_{DSM}	29	A
	T_A=70°C		23	
Avalanche Current C		I_{AS}	77	A
Avalanche energy	L=0.1mH C	E_{AS}	296	mJ
V_{DS} Spike I	10µs	V_{SPIKE}	120	V
Power Dissipation B	T_C=25°C	P_D	326	W
	T_C=100°C		163	
Power Dissipation A	T_A=25°C	P_{DSM}	8.3	W
	T_A=70°C		5.3	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	t ≤ 10s	$R_{\theta JA}$	12	15	°C/W
Maximum Junction-to-Ambient A D	Steady-State		50	60	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	0.36	0.46	°C/W

* Surface mount package TO263(AOB2904)

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA		2.3	2.75	3.3	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A	TO-220		3.6	4.4	mΩ
			T_J=125°C		6.3	7.7	
		V_{GS}=6V, I_D=20A	TO-220		4.1	5.5	mΩ
		V_{GS}=10V, I_D=20A	TO-263		3.4	4.2	mΩ
		V_{GS}=6V, I_D=20A	TO-263		3.9	5.2	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A			90		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V			0.68	1	V
I_S	Maximum Body-Diode Continuous Current [G]					120	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, f=1MHz			7085		pF
C_{oss}	Output Capacitance				605		pF
C_{rss}	Reverse Transfer Capacitance				32		pF
R_g	Gate resistance	f=1MHz		0.7	1.5	2.3	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=50V, I_D=20A			93	135	nC
Q_{gs}	Gate Source Charge				23		nC
Q_{gd}	Gate Drain Charge				16		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=50V, R_L=2.5Ω, R_{GEN}=3Ω			21		ns
t_r	Turn-On Rise Time				22		ns
$t_{D(off)}$	Turn-Off DelayTime				58		ns
t_f	Turn-Off Fall Time				20		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs			49		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs			460		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=175° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
I. L=100uH, Fsw=1Hz, Tj≤150C by repetitive UIS.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

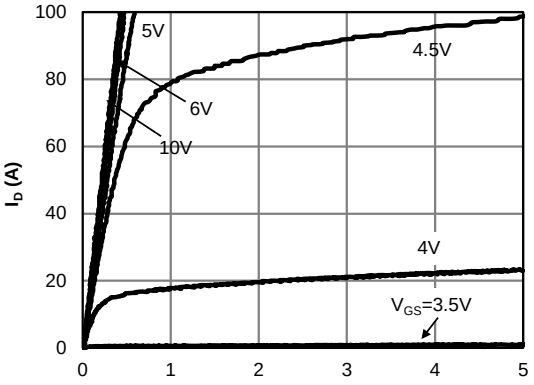


Figure 1: On-Region Characteristics (Note E)

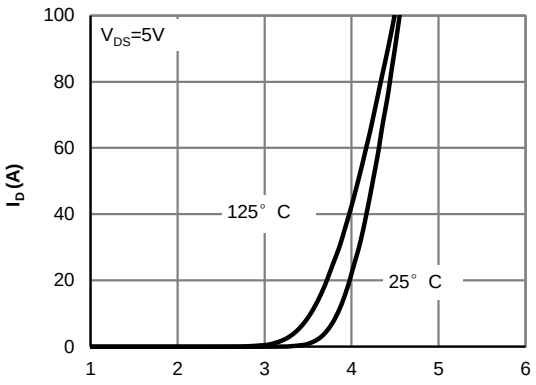


Figure 2: Transfer Characteristics (Note E)

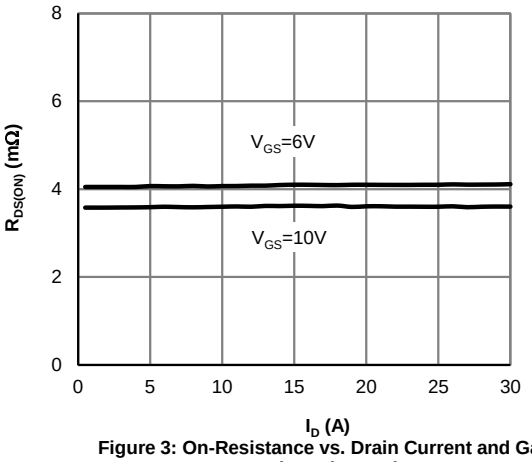


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

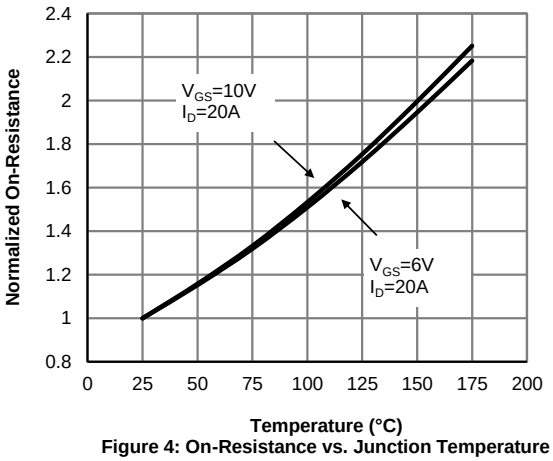


Figure 4: On-Resistance vs. Junction Temperature (Note E)

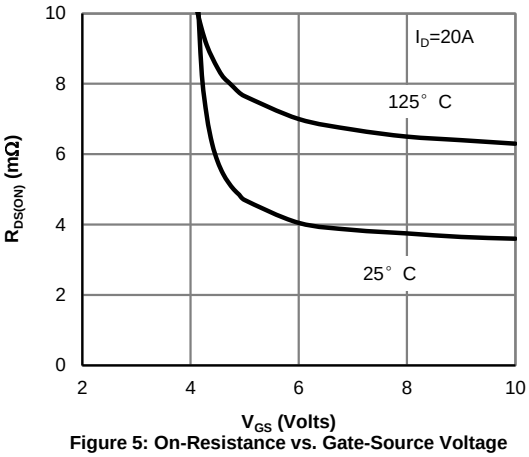


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

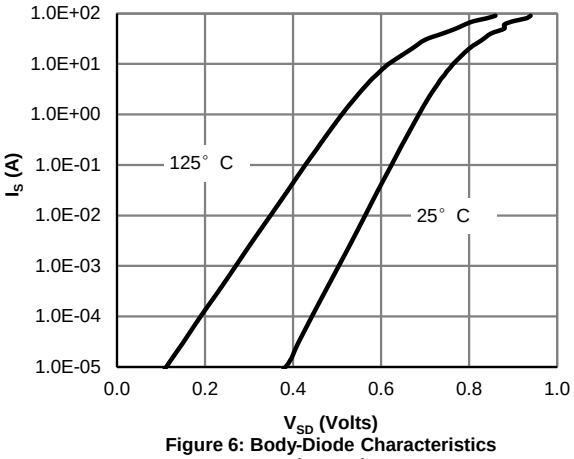


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

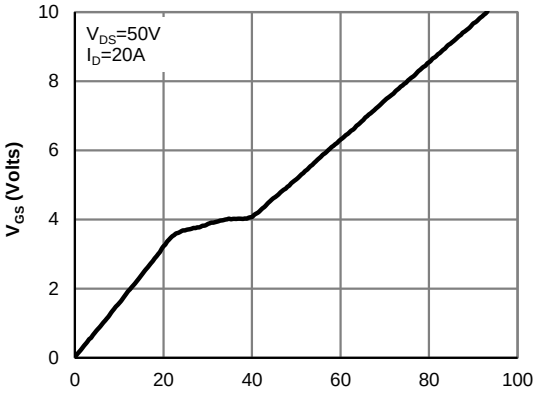


Figure 7: Gate-Charge Characteristics

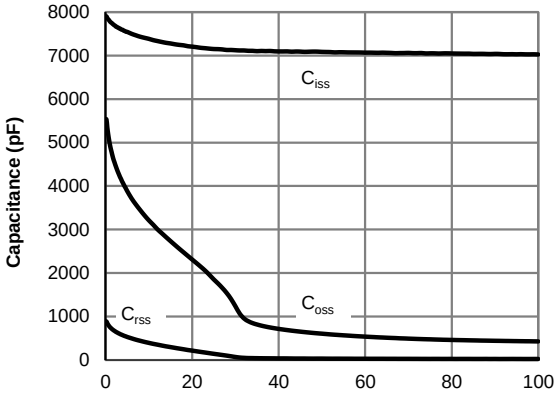
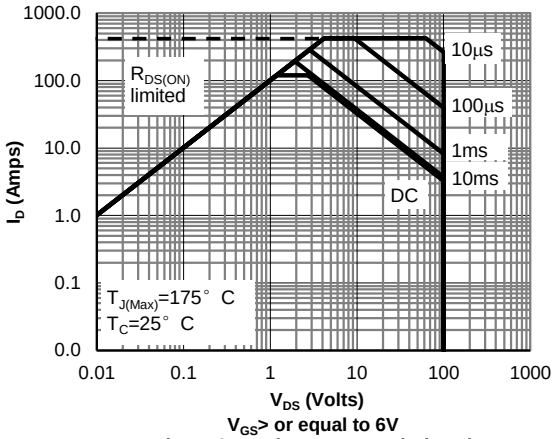


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 6V

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

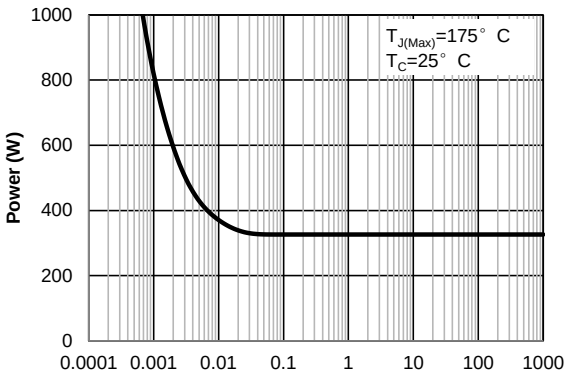


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

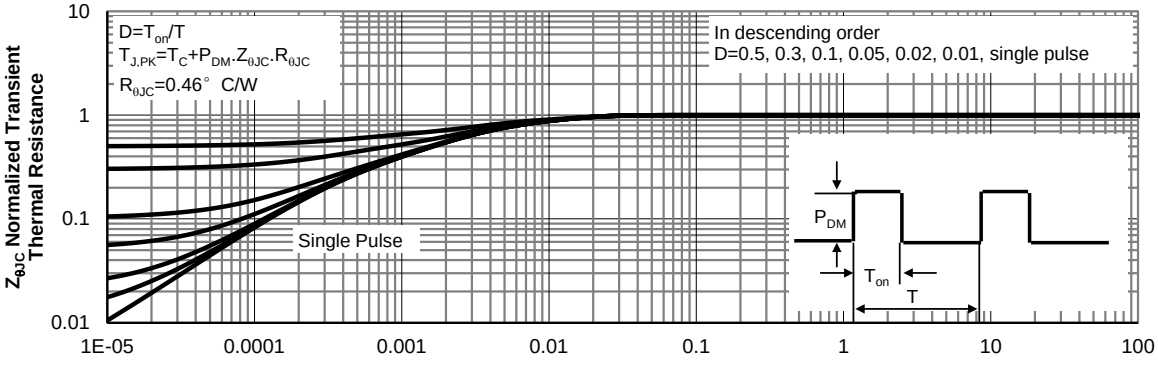


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

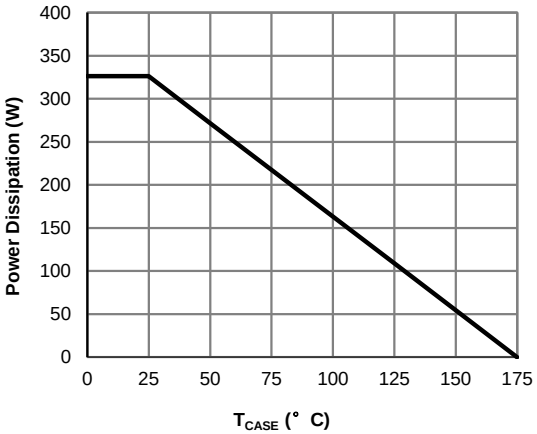


Figure 12: Power De-rating (Note F)

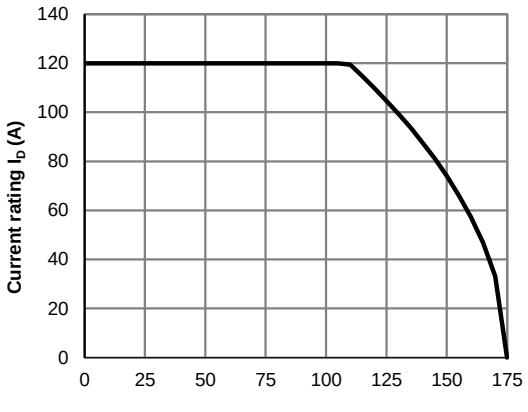


Figure 13: Current De-rating (Note F)

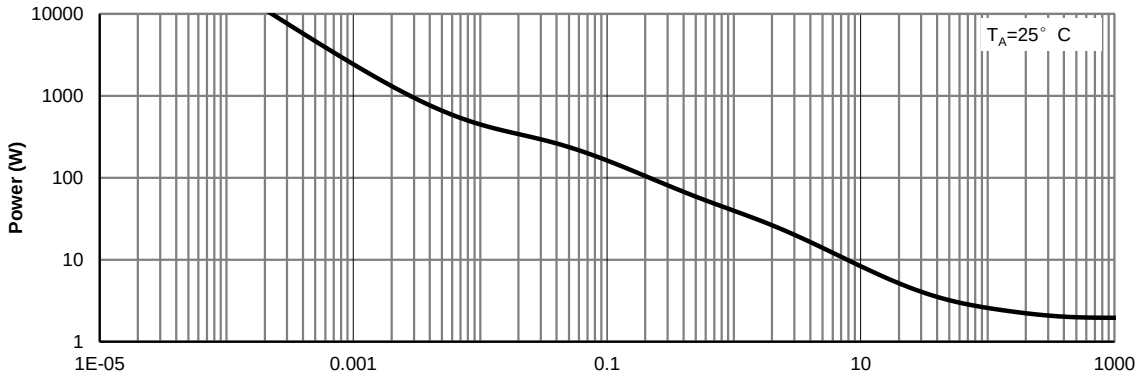


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

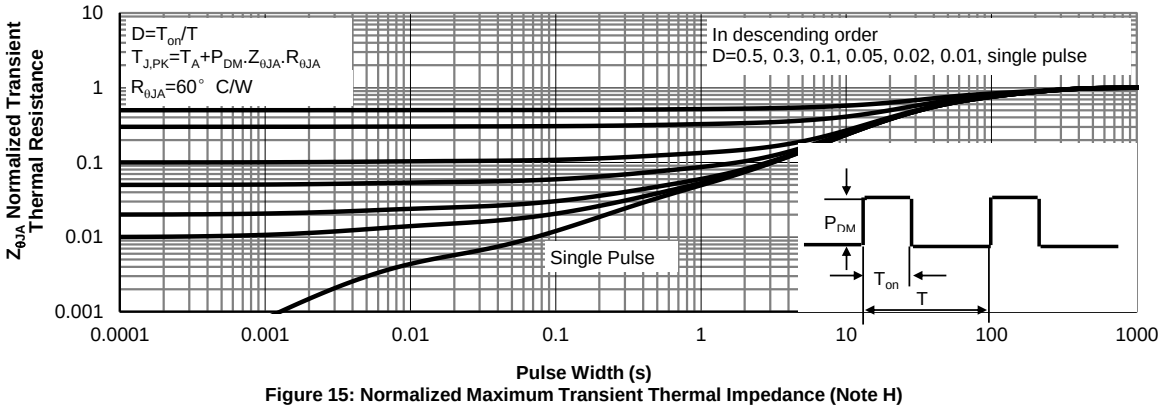


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

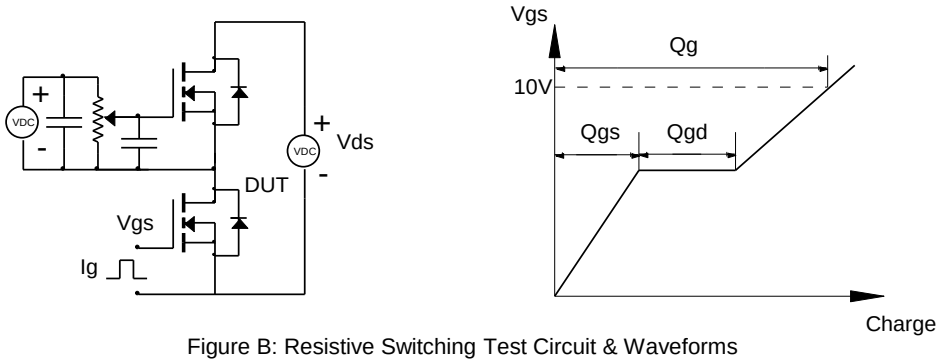


Figure B: Resistive Switching Test Circuit & Waveforms

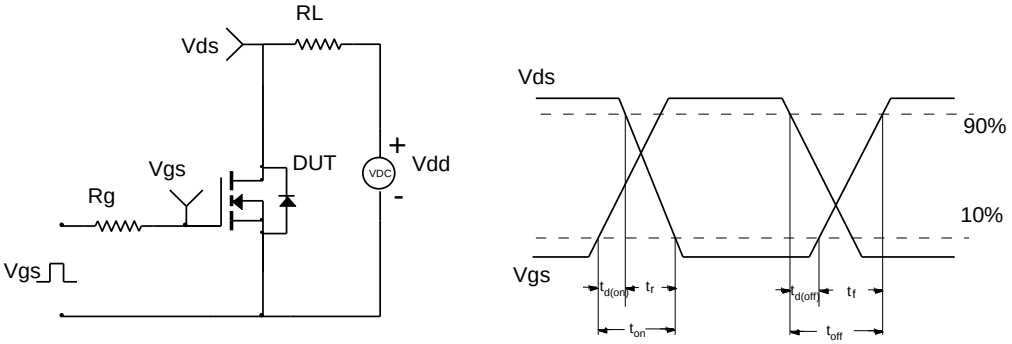


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

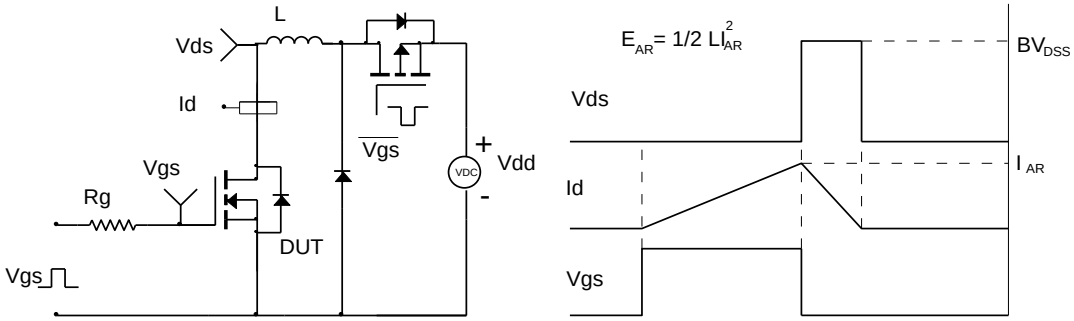


Figure D: Diode Recovery Test Circuit & Waveforms